

Part Number

Customer

| Category | Parameter | Specification | Measurement Method | |
|---------------|-----------|---|--|-----------------------------------|
| OverallWafer | 1.0 | Diameter | 150.00 +/- 0.20 mm | |
| | 2.0 | Primary Flat Orientation | {110} +/- 0.5 degree | Wafer Vendor |
| | 3.0 | Primary Flat Length | 57.50 +/- 2.50 mm | Wafer Vendor |
| | 4.0 | Secondary Flat Orientation | none | |
| | 5.0 | Overall Thickness | 627.00 +/- 25.00 μ m | ADE, 100% |
| | 6.0 | Total Thickness Variation (TTV) | <3.00 μ m | Guaranteed by Process |
| | 7.0 | Bow | <60.00 μ m | ADE to ASTM F534, 20% |
| | 8.0 | Warp | <60.00 μ m | ADE to ASTM F657, 20% |
| | 9.0 | Edge Chips | 0 | Bright Light, 100% (note 2) |
| | 10.0 | Edge Exclusion | 3mm | |
| HandleSilicon | 11.0 | Handle Growth Method | CZ | Wafer Vendor |
| | 12.0 | Handle Orientation | {100} +/- 0.5 degree | Wafer Vendor |
| | 13.0 | Handle Thickness | 525.00 +/- 25.00 μ m | ADE, 100% |
| | 14.0 | Handle Doping Type | N | Wafer Vendor |
| | 15.0 | Handle Dopant | Phosphorous | Wafer Vendor |
| | 16.0 | Handle Resistivity | 1 - 50 Ohmcm | Wafer Vendor |
| | 17.0 | Backside Finish | Polished with lasermark and NO OXIDE | Wafer Vendor |
| BuriedOxide | 18.0 | Oxide Type | Thermal | |
| | 19.0 | Oxide Thickness | 20,000.00 +/- 1,000.00 A | Nanospec centre point, 4% |
| | 20.0 | Oxide formed on | Device Only | Guaranteed by process |
| DeviceSilicon | 21.0 | Device Growth Method | CZ | Wafer Vendor |
| | 22.0 | Device Orientation | {100} +/- 0.5 degree | Wafer Vendor |
| | 23.0 | Nominal Thickness | 100.00 +/- 1.00 μ m | FTIR, 100% 9-Pt (note3) |
| | 24.0 | Distance to device silicon edge from wafer edge | <= 1.5mm | Typical by process |
| | 25.0 | Device Doping Type | N | Wafer Vendor |
| | 26.0 | Device Dopant | Phosphorous | Wafer Vendor |
| | 27.0 | Device Resistivity | 1 - 10 Ohm-cm | Wafer Vendor |
| | 28.0 | Buried Layer Implant | none | implant vendor |
| | 29.0 | Oxygen Concentration | <12.6 ppma | Wafer Vendor |
| | 30.0 | Voids | All wafers scanned for voids by Scanning Acoustic Microscope (SAM) | SAM & Bright Light, 100% (note 2) |
| | 31.0 | Scratches | 0 | Bright Light, 100% (note 2) |
| | 32.0 | Haze | none | Bright Light, 100% (note 2) |

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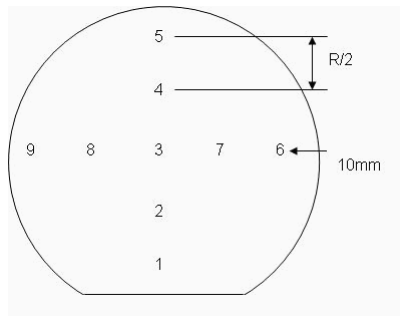
| | | |
|------------------|-------------------|---|
| Shipping Details | Wafer per box : | Max 25 |
| | Packaging : | Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging |
| | Lot Shipment Data | Device Thickness Bow / Warp Data Handle and SOI Thickness |



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information